



# N-Channel NexFET™ Power MOSFET

Check for Samples: CSD16401Q5

## **FEATURES**

- Ultralow Qg and Qgd
- Low Thermal Resistance
- Avalanche Rated
- SON 5-mm × 6-mm Plastic Package

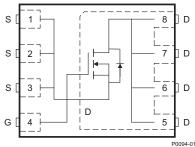
## **APPLICATIONS**

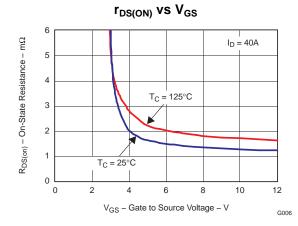
- Point-of-Load Synchronous Buck Converter for Applications in Networking, Telecom and Computing Systems
- Optimized for Synchronous FET Applications

### **DESCRIPTION**

The NexFET™ power MOSFET has been designed to minimize losses in power conversion applications.







#### PRODUCT SUMMARY

V <sub>DS</sub>	Drain-to-source voltage	25		V
$Q_g$	Gate charge, total (4.5 V)	Gate charge, total (4.5 V) 21		nC
$Q_{gd}$	Gate charge, gate-to-drain	5.2		nC
_	Drain-to-source on-resistance	V <sub>GS</sub> = 4.5 V	1.8	mΩ
r <sub>DS(on)</sub>	Diam-to-source on-resistance	V <sub>GS</sub> = 10 V	1.3	mΩ
V <sub>GS(th)</sub>	Threshold voltage	1.5		V

#### ORDERING INFORMATION

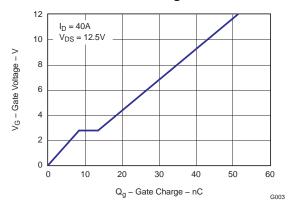
Device	Package	Media	Qty	Ship
CSD16401Q5	SON 5-mm × 6-mm plastic package	13-inch (33-cm) reel	2500	Tape and reel

#### **ABSOLUTE MAXIMUM RATINGS**

$T_A = 2$	5°C unless otherwise stated	VALUE	UNIT
$V_{DS}$	Drain-to-source voltage	25	٧
$V_{GS}$	Gate-to-source voltage	-12 to 16	٧
	Continuous drain current, T <sub>C</sub> = 25°C	100	Α
I <sub>D</sub>	Continuous drain current <sup>(1)</sup>	38	Α
$I_{DM}$	Pulsed drain current, T <sub>A</sub> = 25°C <sup>(2)</sup>	240	Α
$P_D$	Power dissipation <sup>(1)</sup>	3.1	W
$T_J$ , $T_{STG}$	Operating junction and storage temperature range	-55 to 150	ů
E <sub>AS</sub>	Avalanche energy, single-pulse $I_D$ = 100 A, L = 0.1 mH, $R_G$ = 25 $\Omega$	500	mJ

- 1)  $R_{\theta JA} = 40^{\circ} \text{C/W} \text{ on } 1 \text{-in}^2 \text{ (6.45-cm}^2\text{) Cu [2 oz. (0.071-mm thick)] on 0.060-inch (1.52-mm) thick FR4 PCB.}$
- (2) Pulse duration ≤300 µs, duty cycle ≤2%

### **Gate Charge**



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### **ELECTRICAL CHARACTERISTICS**

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$ 

	*C unless otherwise stated)  PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Static C	haracteristics					
BV <sub>DSS</sub>	Drain-to-source voltage	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	25			V
I <sub>DSS</sub>	Drain-to-source leakage current	V <sub>GS</sub> = 0 V, V <sub>DS</sub> = 20 V			1	μΑ
I <sub>GSS</sub>	Gate-to-source leakage current	$V_{DS} = 0 \text{ V}, V_{GS} = -12 \text{ V to } 16 \text{ V}$			100	nA
V <sub>GS(th)</sub>	Gate-to-source threshold voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	1.2	1.5	1.9	V
	Desire to account on marietanes	V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 40 A		1.8	2.3	mΩ
r <sub>DS(on)</sub>	Drain-to-source on-resistance	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 40 A		1.3	1.6	mΩ
9 <sub>fs</sub>	Transconductance	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 40 A		168		S
Dynamic	c Characteristics		<u>.</u>		•	
C <sub>ISS</sub>	Input capacitance			3150	4100	pF
Coss	Output capacitance	V <sub>GS</sub> = 0 V, V <sub>DS</sub> = 12.5 V, f = 1 MHz		2530	3300	pF
C <sub>RSS</sub>	Reverse transfer capacitance			175	230	pF
R <sub>g</sub>	Series gate resistance			1.2	2.4	Ω
Qg	Gate charge total (4.5 V)			21	29	nC
Q <sub>gd</sub>	Gate charge, gate-to-drain	V 40.5 V ID 40.4		5.2		nC
Q <sub>gs</sub>	Gate charge, gate-to-source	V <sub>DS</sub> = 12.5 V, ID = 40 A		8.3		nC
Qg(th)	Gate charge at Vth			4.8		nC
Q <sub>OSS</sub>	Output charge	V <sub>DS</sub> = 15 V, V <sub>GS</sub> = 0 V		55		nC
t <sub>d(on)</sub>	Turnon delay time			16.6		ns
t <sub>r</sub>	Rise time	$V_{DS} = 12.5 \text{ V}, V_{GS} = 4.5 \text{ V}, I_{D} = 40 \text{ A}$		30		ns
t <sub>d(off)</sub>	Turnoff delay time	$V_{GS} = 0 \text{ V}, V_{DS} = 12.5 \text{ V}, f = 1 \text{ MHz}$ $V_{DS} = 12.5 \text{ V}, ID = 40 \text{ A}$ $V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}$		20		ns
t <sub>f</sub>	Fall time			12.7		ns
Diode C	haracteristics	· · · · · · · · · · · · · · · · · · ·	<u> </u>			
$V_{SD}$	Diode forward voltage	I <sub>S</sub> = 40 A, V <sub>GS</sub> = 0 V		0.85	1	V
Q <sub>rr</sub>	Reverse recovery charge	$V_{DD} = 15 \text{ V}, I_F = 40 \text{ A}, di/dt = 300 \text{ A/}\mu\text{s}$		72		nC
t <sub>rr</sub>	Reverse recovery time	$V_{DD} = 15 \text{ V}, I_F = 40 \text{ A}, di/dt = 300 \text{ A/}\mu\text{s}$		45		ns

### THERMAL CHARACTERISTICS

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$ 

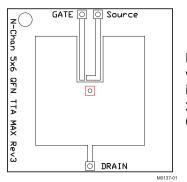
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	PARAMETER	MIN	TYP	MAX	UNIT
R <sub>0</sub> JC	Thermal resistance, junction-to-case (1)			1.1	°C/W
R <sub>e,IA</sub>	Thermal resistance, junction-to-ambient (1) (2)			50	°C/W

R<sub>θJC</sub> is determined with the device mounted on a 1-inch (2.54-cm) square, 2-oz. (0.071-mm thick) Cu pad on a 1.5-inch × 1.5-inch (3.81-cm × 3.81-cm), 0.060-inch (1.52-mm) thick FR4 board. R<sub>θJC</sub> is specified by design, whereas R<sub>θJA</sub> is determined by the user's board design.

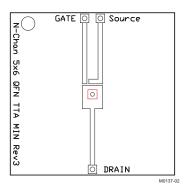
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<sup>(2)</sup> Device mounted on FR4 material with 1 inch<sup>2</sup> (6.45 cm<sup>2</sup>) of 2-oz. (0.071-mm thick) Cu.





Max  $R_{\theta JA} = 50^{\circ} C/W$  when mounted on 1 inch² (6.45 cm²) of 2-oz. (0.071-mm thick) Cu.



Max  $R_{\theta JA} = 121^{\circ} C/W$  when mounted on minimum pad area of 2-oz. (0.071-mm thick) Cu.

## TYPICAL MOSFET CHARACTERISTICS

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$ 

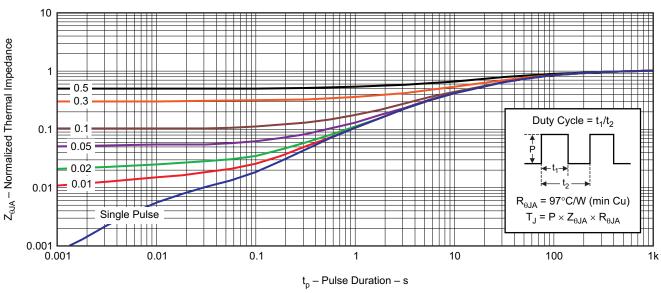


Figure 1. Transient Thermal Impedance

G012



# TYPICAL MOSFET CHARACTERISTICS (continued)

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$ 

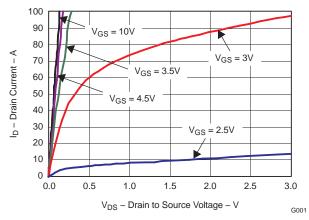


Figure 2. Saturation Characteristics

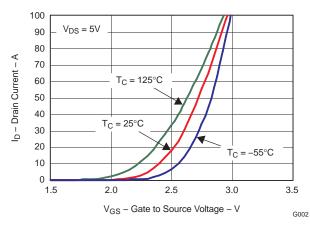


Figure 3. Transfer Characteristics

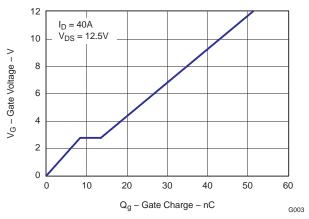


Figure 4. Gate Charge

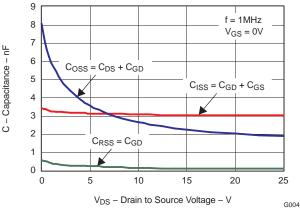


Figure 5. Capacitance

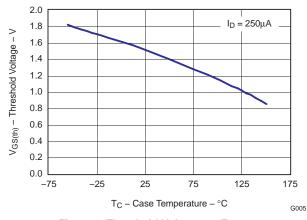


Figure 6. Threshold Voltage vs. Temperature

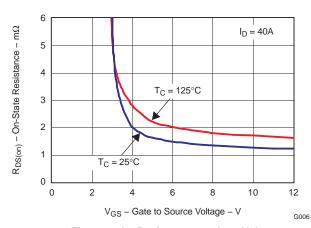


Figure 7. On-Resistance vs. Gate Voltage



# **TYPICAL MOSFET CHARACTERISTICS (continued)**

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$ 

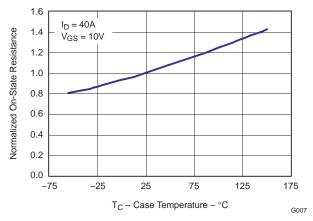


Figure 8. On-Resistance vs. Temperature

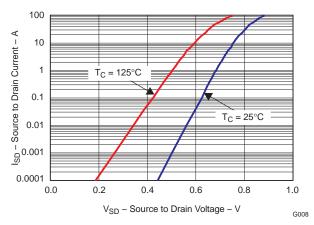


Figure 9. Typical Diode Forward Voltage

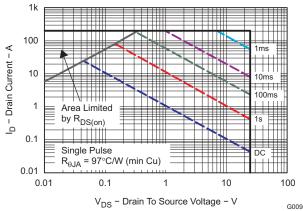


Figure 10. Maximum Safe Operating Area

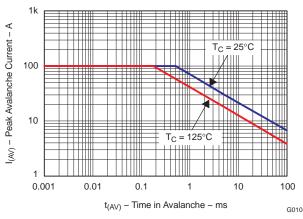


Figure 11. Single-Pulse Unclamped Inductive Switching

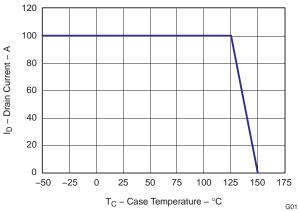
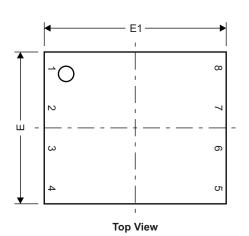


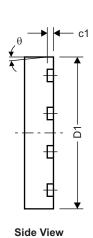
Figure 12. Maximum Drain Current vs. Temperature

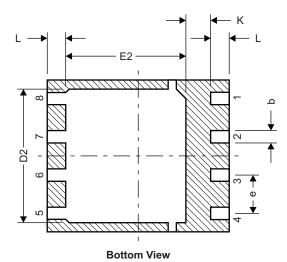


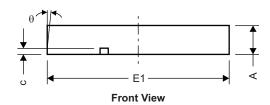
# **MECHANICAL DATA**

# **Q5 Package Dimensions**









M0140-01

DIM	MILLIM	ETERS	INCHES		
DIW	MIN	MAX	MIN	MAX	
Α	0.950	1.050	0.037	0.039	
b	0.360	0.460	0.014	0.018	
С	0.150	0.250	0.006	0.010	
c1	0.150	0.250	0.006	0.010	
D1	4.900	5.100	0.193	0.201	
D2	4.320	4.520	0.170	0.178	
E	4.900	5.100	0.193	0.201	
E1	5.900	6.100	0.232	0.240	
E2	3.920	4.12	0.154	0.162	
е	1.27	TYP	0.0	050	
K	0.760		0.030		
L	0.510	0.710	0.020	0.028	
θ	0.00				

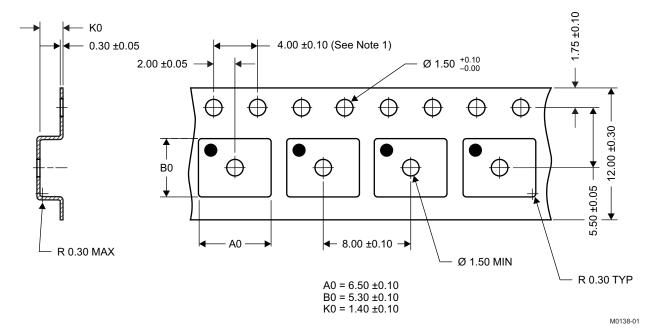


Recommended PCB	Pattern
F6 - F1	F7
84 F10	M0139-01  4  7  4  8  8  8  8  9  1  1  1  1  1  1  1  1  1  1  1  1

DIM	MILLIN	IETERS	INC	HES	
DIM	MIN	MAX	MIN	MAX	
F1	6.205	6.305	0.244	0.248	
F2	4.460	4.560	0.176	0.180	
F3	4.460	4.560	0.176	0.180	
F4	0.650	0.700	0.026	0.028	
F5	0.620	0.670	0.024	0.026	
F6	0.630	0.680	0.025	0.027	
F7	0.700	0.800	0.028	0.031	
F8	0.650	0.700	0.026	0.028	
F9	0.620	0.670	0.024	0.026	
F10	4.900	5.000	0.193	0.197	
F11	4.460	4.560	0.176	0.180	

For recommended circuit layout for PCB designs, see application note SLPA005 – Reducing Ringing Through PCB Layout Techniques.

## **Q5 Tape and Reel Information**



#### Notes:

- 1. 10 sprocket hole pitch cumulative tolerance ±0.2
- 2. Camber not to exceed 1 mm IN 100 mm, noncumulative over 250 mm
- 3. Material:black static dissipative polystyrene
- 4. All dimensions are in mm (unless otherwise specified)
- 5. A0 and B0 measured on a plane 0.3 mm above the bottom of the pocket
- 6. MSL1 260°C (IR and Convection) PbF Reflow Compatible



# **REVISION HISTORY**

C	Changes from Revision Original (August 2009) to Revision A  Deleted environmental bullets from Features list			
•	Deleted environmental bullets from Features list	1		
•	Deleted Package Marking Information section at the end of the data sheet	7		

# PACKAGE MATERIALS INFORMATION

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# TAPE AND REEL INFORMATION





A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

# QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



### \*All dimensions are nominal

	Device	Package Type	Package Drawing			Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
I	CSD16401Q5	SON	DQH	8	2500	330.0	12.8	6.5	5.3	1.4	8.0	12.0	Q1

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#### \*All dimensions are nominal

Device	Device Package Type		Package Drawing Pins SPQ			Width (mm)	Height (mm)	
CSD16401Q5	SON	DQH	8	2500	335.0	335.0	32.0	

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